

Features

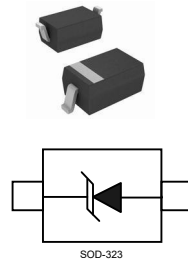
- 360Watts peak pulse power ($t_p = 8/20\mu s$)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 $\pm 30kV$ contact $\pm 30kV$ air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 30A (8/20 μs)

Applications

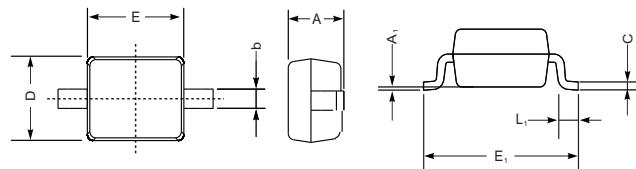
- USB Vbus,
- Power Line
- Power management

Mechanical Data

- SOD323 package
- Molding compound flammability rating: UL94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant



SOD323



UNIT		A	C	D	E	E ₁	b	L ₁	A ₁
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—
mil	max	43	5.9	55	70	108	16	16	8
	min	32	3.1	47	63	100	9.8	7.9	—

Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ($t_p = 8/20\mu s$)	P_{PP}	360	Watts
Peak Pulse Current ($t_p = 8/20\mu s$) (note1)	I_{pp}	30	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V_{ESD}	30 30	kV
Lead Soldering Temperature	T_L	260(10seconds)	°C
Junction Temperature	T_J	-55 to + 150	°C
Storage Temperature	T_{stg}	-55 to + 150	°C

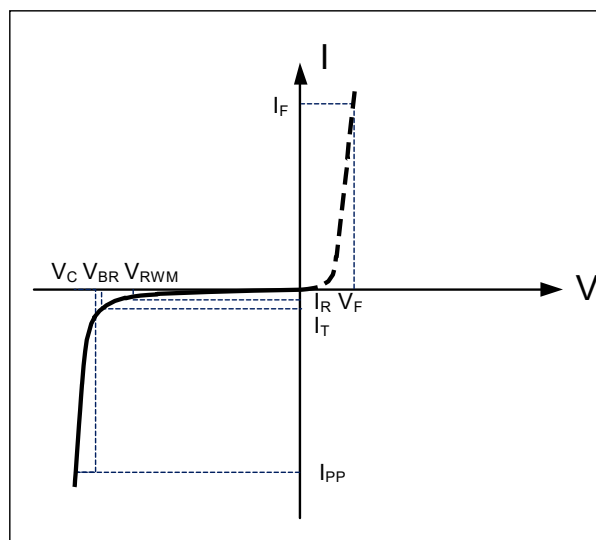
CESD3V3D3

Electrical Characteristics

Parameter	Symbol	Conditions	Min	Typical	Max	Units
Reverse Stand-Off Voltage	V_{RWM}				3.3	V
Reverse Breakdown Voltage	V_{BR}	$I_T=1mA$	5.0			V
Reverse Leakage Current	I_R	$V_{RWM}=3.3V, T=25^{\circ}C$			1.0	μA
Clamping Voltage	V_C	$I_{PP}=30A, t_p=8/20\mu s$		10		V
Junction Capacitance	C_j	$V_R = 0V, f = 1MHz$		300		pF

Electrical Parameters (TA = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current



Note: 8/20 μs pulse waveform.

RATING AND CHARACTERISTIC CURVES (CESD3V3D3)

Figure 1: Peak Pulse Power vs. Pulse Time

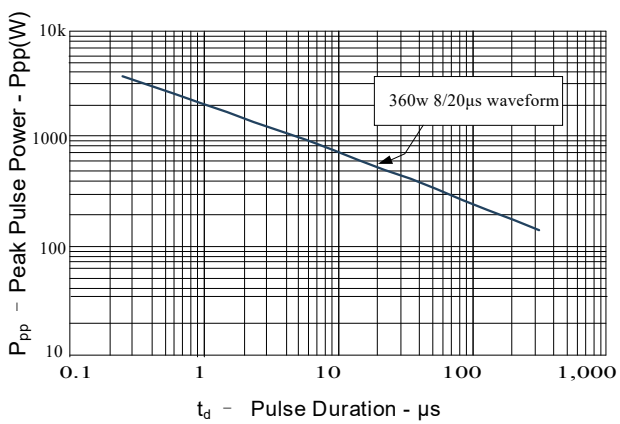


Figure 2: Power Derating Curve

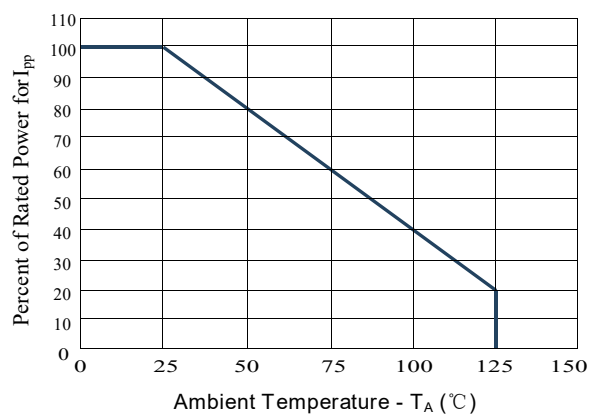


Figure 3: Pulse Waveform

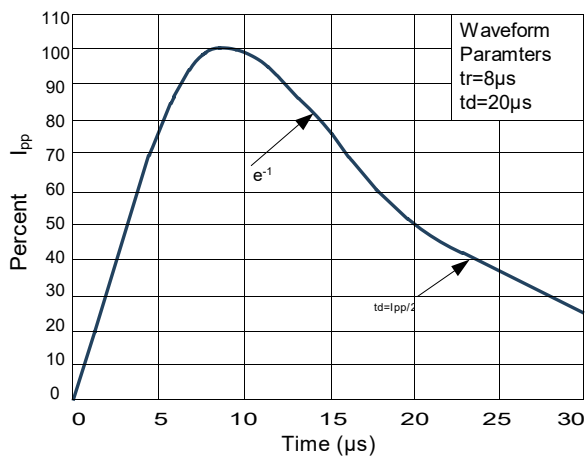


Figure 4: Clamping Voltage vs. I_pp

